

ABSTRACT

LASER PROCESSING METHOD OF WAFER

There is provided a laser processing method of a wafer in which a wafer segmented by plural planned dividing lines set on a surface in a lattice manner is processed by using a laser processing apparatus including a laser beam irradiation unit that irradiates, through a collecting lens, the wafer held by a chuck table with plural laser beams formed by being oscillated by a laser beam oscillator and being split by a laser beam splitting unit. The laser processing method includes a processed groove forming step of irradiating the wafer with the plural laser beams along the planned dividing line and forming a processed groove along the planned dividing line in the wafer. In the processed groove forming step, the plural laser beams split by the laser beam splitting unit are arranged in a line manner along a direction that is non-parallel to an extension direction of the planned dividing line irradiated with the plural laser beams.

(Figure 3B)